BTA216X series D, E and F

GENERAL DESCRIPTION

QUICK REFERENCE DATA

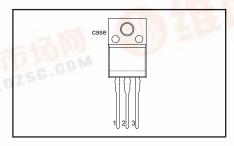
Passivated guaranteed commutation triacs in a full pack, plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance of requirements commutation performance and gate sensitivity. The 'sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

SYMBOL	PARAMETER	MAX.	MAX.	UNIT	
V _{DRM}	BTA216X- BTA216X- BTA216X- Repetitive peak off-state voltages	600D 600E 600F 600	800E 800F 800	V	
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	16 140	16 140	A A	
N CONFIGURATION SYMBOL					

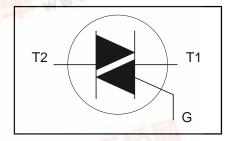
PINNING - SOT186A

PIN	DESCRIPTION			
1	main terminal 1			
2	main terminal 2			
3	gate			
case	isolated			

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MA	X.	UNIT
V_{DRM}	Repetitive peak off-state voltages	THE COM	9 =	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-	16		Α
I _{TSM}	Non-repetitive peak on-state current	$T_{hs} \le 38 ^{\circ}\text{C}$ full sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge				
		t = 20 ms t = 16.7 ms	-	14		A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of	t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$	4	150 98 100		A A²s A/μs
I _{GM} V _{GM} P _{GM} P _{G(AV)}	on-state current after triggering Peak gate current Peak gate voltage Peak gate power Average gate power	$dI_{G}/dt = 0.2 \text{ A/}\mu\text{s}$ - 2 5 5 5			A V W	
T _{stg} T _j	Storage temperature Operating junction temperature		-40 -	15 12	္ငံ	

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	ı	ı	2500	>
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	ı	10	1	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound			4.0 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.		MAX.		UNIT
		BTA216X-		D	D	Е	F	
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ T2+ G+	-	1.3	5	10	25	mA
		T2+ G- T2- G-	- -	2.6 3.4	5 5	10 10	25 25	mA mA
I IL	Latching current	$V_D = 12 \text{ V; } I_{GT} = 0.1 \text{ A}$ $T2+ G+$ $T2+ G T2- G-$	- - -	10.2 11.3 19.3	15 25 25	25 30 30	30 40 40	mA mA mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	8	15	25	30	mA
					D, E, F			
$V_{\rm GT}$	On-state voltage Gate trigger voltage	$I_T = 20 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	- - 0.25	1.2 0.7 0.4		1.5 1.5		V V V
I _D	Off-state leakage current	$V_D = 400 \text{ V}, I_T = 0.1 \text{ A},$ $T_j = 125 \text{ C}$ $V_D = V_{DRM(max)};$ $T_j = 125 \text{ C}$	-	0.4		0.5		mA

² Device does not trigger in the T2-, G+ quadrant.

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DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
		BTA216X-	D	Е	F	D		
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 110 °C; exponential waveform; gate open circuit	30	60	70	65	-	V/μs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V; } T_j = 110 \text{ °C;}$ $I_{T(RMS)} = 16 \text{ A;}$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s; gate}$ open circuit	2.5	4.7	9.5	7.5	-	A/ms
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 110 \text{ °C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 0.1 \text{ V}/\mu\text{s}; \text{ gate}$ open circuit	12	40	50	100	-	A/ms
					D, E, F	•		
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	-	-	-	2	-	μs

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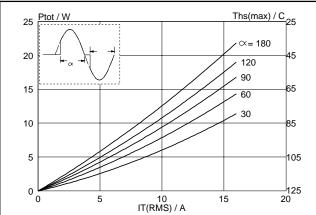
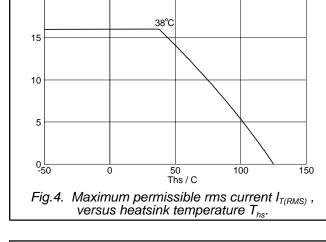


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.



IT(RMS) / A

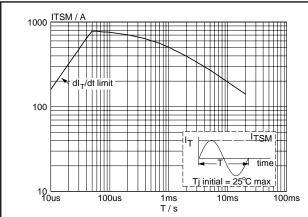


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

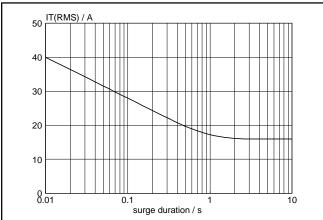


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38 ^{\circ}\text{C}$.

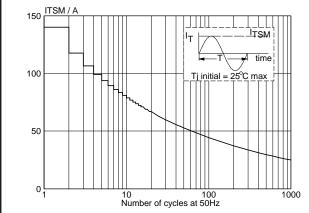


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

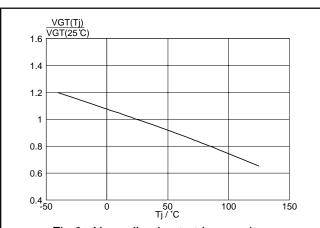
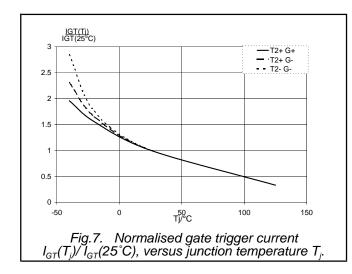
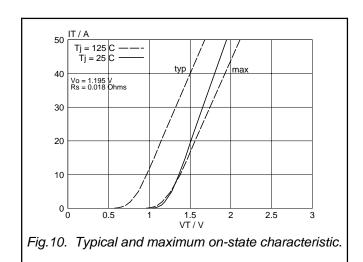
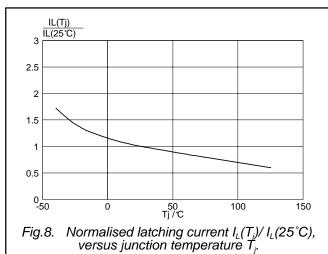


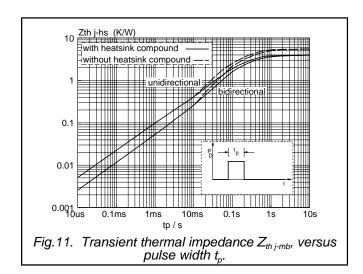
Fig.6. Normalised gate trigger voltage $V_{\rm GT}(T_{\rm j})/V_{\rm GT}(25\,^{\circ}{\rm C})$, versus junction temperature $T_{\rm j}$.

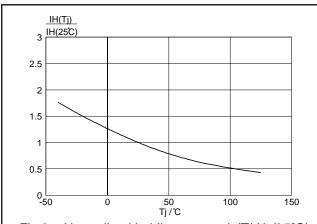
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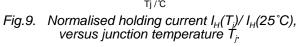












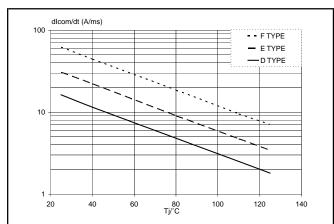
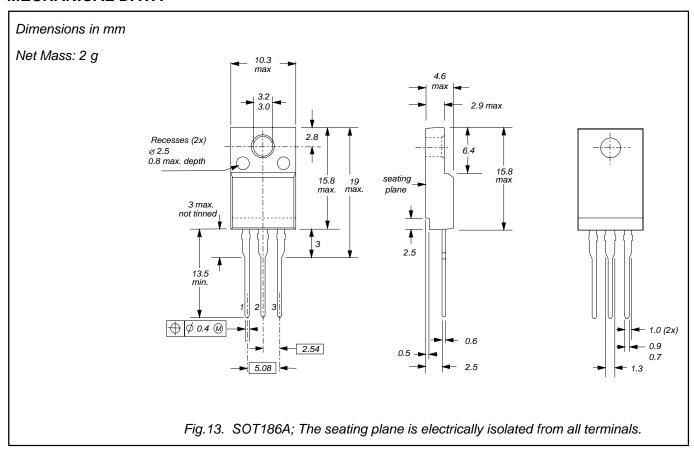


Fig. 12. Minimum, critical rate of change of commutating current dl_{com}/dt versus junction temperature, $dV_{com}/dt = 20V/\mu s$.

BTA216X series D, E and F

MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

BTA216X series D, E and F

DEFINITIONS

Data sheet status						
Objective specification	This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.					
Product specification	This data sheet contains final product specifications.					
1						

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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